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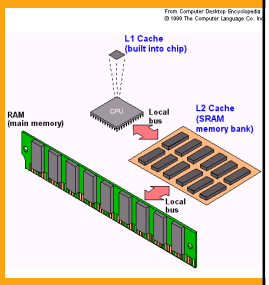
Lecture 4

Internal Memory Cache

Stallings: Ch 4, Ch 5
Key Characteristics
Locality
Cache
Main Memory



Key Characterics of Memories / Storage

Location	**Performance**
Processor	Access time
Internal (main)	Cycle time
External (secondary)	Transfer rate
Capacity	**Physical Type**
Word size	Semiconductor
Number of words	Magnetic
Unit of Transfer	Optical
Word	Magneto-Optical
Block	**Physical Characteristics**
Access Method	Volatile/nonvolatile
Sequential	Erasable/nonerasable
Direct	**Organization**
Random	
Associative	

(Sta06 Table 4.1)

Goals

- I want my memory lightning fast
- I want my memory to be gigantic in size

- Register access viewpoint
  - data access as fast as HW register
  - **data size as large as memory**

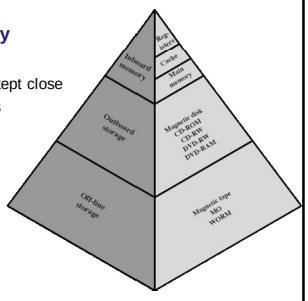
cache
HW solution

- Memory access viewpoint
  - data access as fast as memory
  - **data size as large as disk**

virtual memory
HW help for SW solution

Memory Hierarchy

- Most often needed data kept close
- Access to small data sets can be made fast
  - simpler circuits
  - smaller gate delays
- Faster ~ more expensive
- Large can be bigger and cheaper (per B)



up: smaller, faster, more expensive, more frequent access
down: bigger, slower, less expensive, less frequent access

(Sta06 Fig 4.1)

Principle of locality (*paikallisuus*)

- In any given time period, memory references occur only to a small subset of the whole address space

= The reason why memory hierarchies work

Prob (small data set) = 99%
Prob (the rest) = 1%

"Cost" (small data set) = 2 µs
"Cost" (the rest) = 20 µs

Aver cost = 99% * 2 µs + 1% * 20 µs = 2.2 µs

- Average cost is close to the cost of small data set
- How to determine data for that small set?
- How to keep track of it?

Sta06 Fig 4.2

Principle of locality

- In any given time period
  - memory references occur only to a small subset of the whole address space
- Temporal locality (*ajallinen*)
  - it is likely that a data item referenced a short time ago will be referenced again soon
- Spatial locality (*alueellinen*)
  - it is likely that a data items close to the one referenced a short time ago will be referenced soon

MEM:

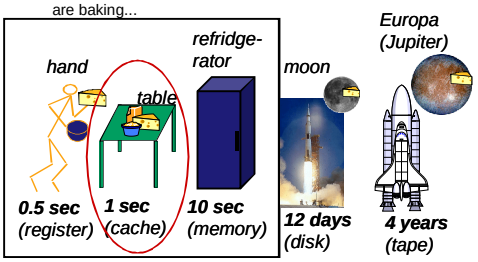
345	23	71	8	305	63	91	2

Computer Organization II

Cache

Teemu's Cheesecake

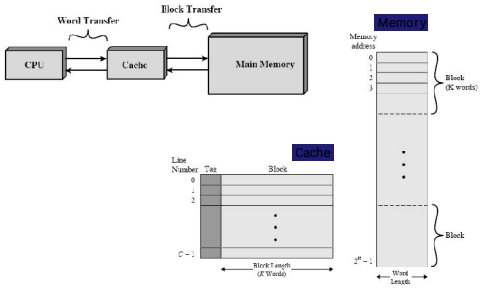
Register, on-chip cache, memory, disk, and tape speeds relative to times locating cheese for the cheese cake you are baking...



Cache Memory (*välimuisti*)

- How to access main memory as fast as registers?
- Locality → Use (CPU) cache!
  - Keep most probably referenced data in fast cache close to processor, and rest in memory
  - Most of data accesses only to cache
    - hit ratio 0.9-0.99
  - Cache is much smaller than main memory
  - Cache is (much) more expensive (per byte) than memory

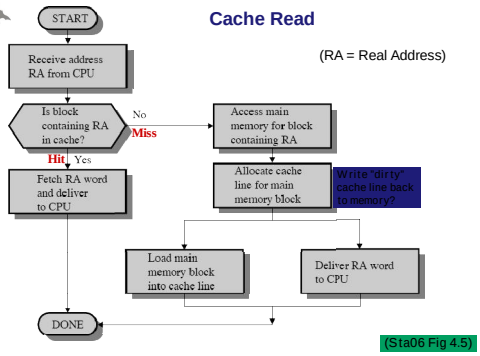
Cache



(Sta06 Fig 4.3, 4.4)

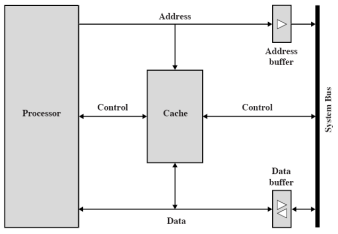
Cache Read

(RA = Real Address)



(Sta06 Fig 4.5)

Cache Organization



(Sta06 Fig 4.6)

Cache Design

Cache Size	**Write Policy**
Mapping Function	Write through
Direct	Write back
Associative	Write once
Set Associative	**Line Size**
Replacement Algorithm	**Number of caches**
Least recently used (LRU)	Single or two level
First in first out (FIFO)	Unified or split
Least frequently used (LFU)	
Random	

- Cache Size & Line Size
  - Many blocks help for temporal locality
  - Large blocks help for spatial locality
  - Larger cache is slower
  - Multi-level cache

Typical sizes:
L1: 8 KB – 64 KB
L2: 256KB - 8 MB

(Sta06 Table 4.2)

Mapping

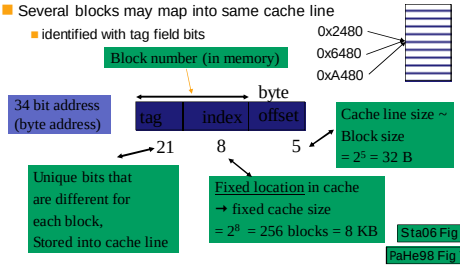
- Which block contains the memory location?
- Is the block in cache?
- Where is it located?

- Solutions
  - direct mapping (suora kuvaus)
  - fully associative mapping (täysin assosiatiivinen)
  - set associative mapping (joukkoassosiatiivinen)

Cache simulation tools:
http://www.ecs.umass.edu/ece/koren/architecture/Cache/frame0.htm

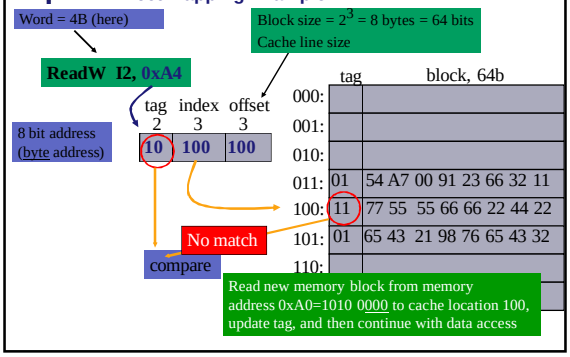
Direct Mapping

- Each block has only one possible location (line) in cache
  - determined by index field bits
- Several blocks may map into same cache line
  - identified with tag field bits

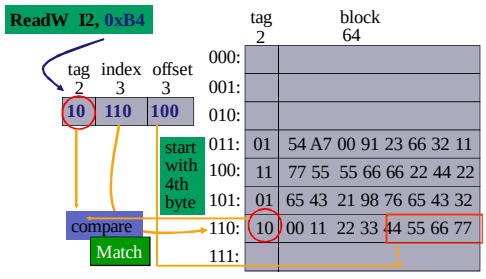


Sta06 Fig 4.7
PaHe98 Fig 7.10

Direct Mapping Example

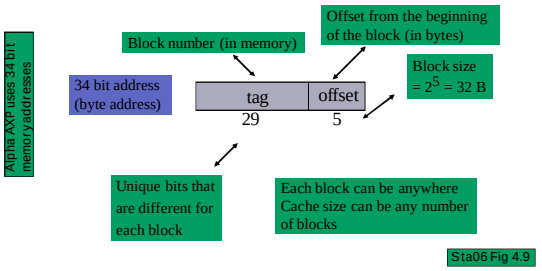


Direct Mapping Example 2



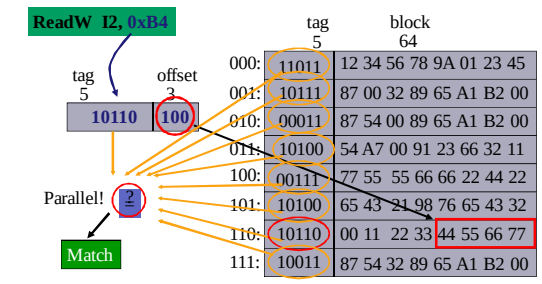
Fully Associative Mapping (6)

- Each block can be in any cache line
  - tag must be complete block number



Sta06 Fig 4.9

Fully Associative Example

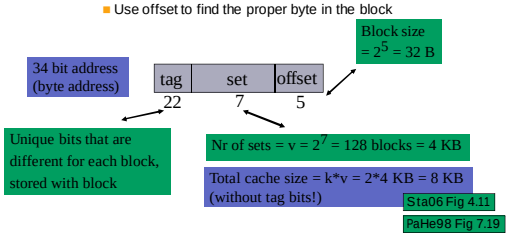


Fully Associative Mapping

- Lots of circuits
  - tag fields are long - wasted space?
  - each cache line tag must be compared parallelly
  - with the memory address tag
    - lots of wires, comparison circuits
    - large surface area on chip
- Final comparison "or" has large gate delay
  - did any of these 64 comparisons match?
    - log2(64) = 6 levels of binary OR-gates
  - how about 262144 comparisons?
    - 18 levels?
- ⇨ Can use it only for small caches

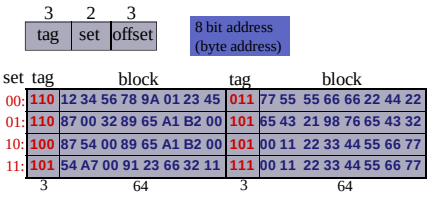
Set Associative Mapping

- With set size k=2, each cache entry contain 2 blocks
  - Use set (set index) field to find the cache entry
  - Use tag to determine if the block belongs to the set
  - Use offset to find the proper byte in the block

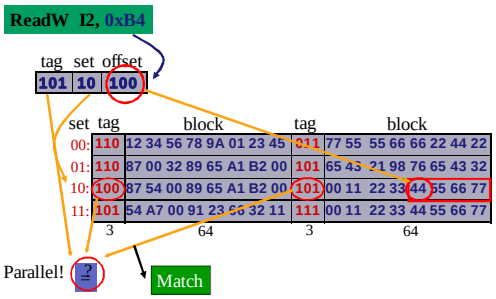


2-way Set Associative Cache

- k=2 → Two blocks in each set (= in one cache entry)
- 4 sets → 2 bits for set index
- 2 words in a block = 8 Bytes → 3 bits for byte offset
- 3 bits for tag



2-way Set Assoc. Cache Example



Set Associative Mapping

- Set associative cache with set size k=2
  = 2-way cache (common)
- Degree of associativity = nbr of blocks in a set = v
  - Large degree of associativity?
    - More data items in one set
    - Less "collisions" within set
    - Final comparison (matching tags?) gate delay?
  - Maximum (nr of cache lines)
    ⇨ fully associative mapping — Whole cache is one set!
  - Minimum (1)
    ⇨ direct mapping — Each cache line is a set!

Cache Replacement Algorithm

- Which cache block to replace to make room for new block from memory?
- Direct mapping: trivial
- First-In-First-Out (FIFO)?
- Least-Frequently-Used (LFU)?
- Random?
- Which one is best / possible?
  - Chip area?
  - Fast? Easy to implement?

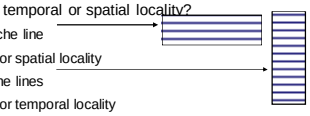
Cache Write Policy – memory writes?

- Write through (*läpikirjoittava*)
  - Each write goes always to cache and memory
  - Each write is a cache miss!
- Write back (*lopuksi/takaisin kirjoittava*)
  - Each write goes only to cache
  - Write cache block back to memory
  - only when it is replaced in cache — A bit set
  - Memory may have stale (old) data
  - cache coherence problem (*yhdenmukaisuus, yhtäpitävyys*)
- Write once (*"vain kerran kirjoittava?"*)
  - Write-invalidate Snoopy-cache coherence protocol for multiprocessors
  - Write invalidates data in other caches
  - Write to memory at replacement time, or when some other cache needs it (has read/write miss)

Coherence problems:
- More users of the same data: memory valid? cache valid?
- multiple processors with own caches

Cache Line Size

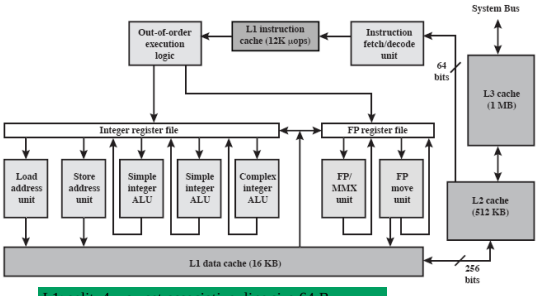
- How big cache line?
- Optimise for temporal or spatial locality?
  - bigger cache line
    - ⇨ better for spatial locality
  - more cache lines
    - ⇨ better for temporal locality
- Best size varies with program or program phase?
- Best size different with code and data?
- 2-8 words?
  - word = 1 float??



Types and Number of Caches

- Same cache for data and code, or not?
  - Data references and code references behave differently
- Unified vs. split cache (yhdistetty/erilliset)
  - split cache: can optimise structure separately for data and code — Trend towards split caches: Pentium, Power PC... (instruction pipelining)
- One cache too large for best results
- Multiple levels of caches
  - L1 on same chip as CPU
  - L2 on same package or chip as CPU
    - older systems: same board
  - L3 on same board as CPU

Example: Pentium 4 Block Diagram



L1: split, 4-way set-associative, line size 64 B
L2, L3: unified, 8-way set-associative, line size 128 B

(Sta06 Fig 4.13)

Computer Organization II

Main Memory

Main Memory Types

Memory Type	Category	Erasure	Write Mechanism	Volatility
Random-access memory (RAM)	Read-write memory	Electrically, byte-level	Electrically	Volatile
Read-only memory (ROM)	Read-only memory	Not possible	Masks	Nonvolatile
Programmable ROM (PROM)			Electrically	
Erasable PROM (EPROM)	Read-mostly memory	UV light, chip-level		
Electrically Erasable PROM (EEPROM)		Electrically, byte-level		
Flash memory		Electrically, block-level		

(Sta06 Table 5.1)

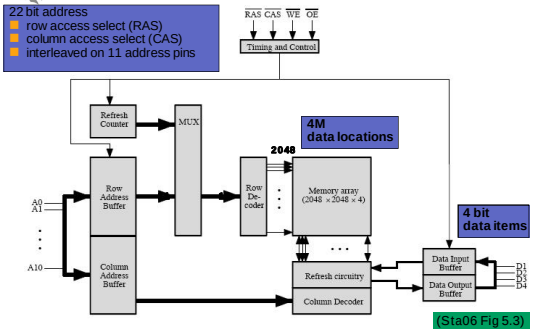
- Random access semiconductor memory
  - Direct access to each memory cell
  - Access time same for all cells

RAM

- Dynamic RAM, DRAM — Analog: Charge on capacitors
  - Periodic refreshing required
  - Refresh required after read
  - Simpler, slower, denser, bigger (bytes per chip)
  - Access time ~ 60 ns
  - Main memory? (early systems)
- Static RAM, SRAM — Digital: flip-flop gates
  - No periodic refreshing needed
  - Data remains until power is lost
  - More complex (more chip area/byte), faster, smaller
  - Access time ~ 2-5 ns
  - Level 2 cache?

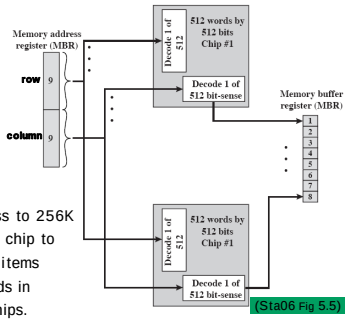
DRAM Access, 16 Mb DRAM (4M x 4)

22 bit address
- row access select (RAS)
- column access select (CAS)
- interleaved on 11 address pins



(Sta06 Fig 5.3)

256-KB DRAM Memory Organization



- Simultaneous access to 256K 8-bit word memory chip to access larger data items
- Access 64-bit words in parallel? Need 8 chips.

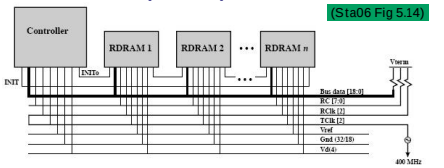
(Sta06 Fig 5.5)

SDRAM (Synchronous DRAM)

- CPU clock synchronizes also the bus
  - Runs on higher clock speeds than ordinary DRAM
  - CPU knows how long it takes to make a reference,
  - can do other work while waiting
- 16 bits in parallel
  - Access 4 DRAMs (4 bits each) in parallel
  - Access time ~ 18 ns, transfer rate ~ 1.3 GB/s
- DDR SDRAM, double data rate
  - Current main memory technology
  - Supports transfers both on rising and falling edge of the clock cycle
  - Consumes less power
  - Access time ~ 12 ns, transfer rate ~ 3.2 GB/s

Rambus DRAM (RDRAM)

(Sta06 Fig 5.14)



- Works with fast Rambus memory bus (800Mbps)
  - Controller + RDRAM modules
  - Access time ~ 12 ns, transfer rate ~ 4.8 GB/s
- Speed slows down with many memory modules
  - Serially connected on Rambus channel
  - Not good for servers with 1 GB memory (for now!)

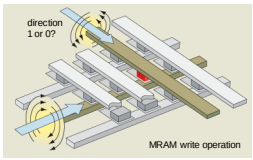
STI Cell processor

Flash memory

- Based on transistors that are separated by a thin oxide layer
  - Flash cell is analog, not digital storage: uses different charge levels to store 2 (or more) bits in each cell
- Non-volatile, data remains with power off
  - Electrical erasing in blocks = "flash"
  - Slow to write
  - Access time ~ 50 ns
- Used as a solid state storage
  - No moving parts
  - FlashBIOS in PC's, USB-memory
  - In phones, digital cameras, hand-held devices,....

MRAM

- Magnetoresistive Random Access Memory (MRAM)
  - Data stored with magnetic fields on two plates
  - Magnetic field directions determine bit value
- Non-volatile, data remains with power off
  - Fast to read/write
  - No upper limit for write counts (Flash has upper limit)
  - Access time comparable to DRAM
  - Almost as fast as SRAM
- Future open
  - Small market share now
  - Expensive now (2006: $25 4Mbit)
  - Still under development
  - May replace flash in a few years
  - May replace SRAM later on
  - May replace DRAM and become "universal memory"



http://www.research.ibm.com/journal/rd/501/maffitt.html

Kertauskysymyksiä/Review questions

- Memory hierarcy and principle of locality?
- Different ways to use locality in cache solutions?
- Differences of associative and set associative mappings?
- Why to have separate caches for instructions and data ?

- Muistihierarkia ja paikallisuus?
- Millä tavoin paikallisuutta huomiodaan välimuistiratkaisussa?
- Assosiatiivisen ja joukkoassosiatiivisen kuvauksen erot?
- Miksi käskyille oma välimuisti ja datalle oma?